# Contents

Abstract (in Chinese)  

Abstract (in English)  

Acknowledgement  

Contents  

Figure Captions  

Table Captions  

### Chapter 1  

**Introduction**  

1.1 Introduction of Device Technology  

1.2 PHEMT Performance Improvement by Schottky barrier layer  

1.3 Gate orientation dependence of InAlP/InGaAs PHEMTs  

1.4 Outline of this study  

### Chapter 2  

**Study of Schottky Contacts on InAlP**  

2.1 Theory of Schottky Contacts  

2.2 Interfacial Reaction between Semiconductor and Schottky metal  

2.3 Use Pt as schottky contact metal for E-mode device fabrication
Chapter 3  Device structure and Fabrication  19

3.1  Device Structure  19

3.2  Device Fabrication  19

3.2.1  Wafer Cleaning  20

3.2.2  Device Isolation  20

3.2.3  Ohmic Contact  20

3.2.4  Gate Formation  21

3.2.5  Selective Etching for Gate Recess  21

3.2.6  Device passivation and contact via formation  22

3.3  Schottky diode fabrication  23

3.4  InAlP/InGaAs PHEMTs with Ti/Pt/Au, Pt/Ti/Pt/Au and W/Ti/Pt/Au schottky contacts  23

3.5  Characteristics and Measurements  24

3.5.1  Specific contact resistivity  24

3.5.2  Breakdown voltage ($V_B$)  25

3.5.3  Transconductance ($G_m$)  25

3.5.4  Pinch off voltage($V_P$)/ Threshold voltage($V_T$)  26

3.6  Gate orientation  26

Chapter 4  Experimental Results and Discussion  27

4.1  Mesa Isolation  27

4.2  Ohmic contact  27

4.3  Optical gate  28

4.4  Selective etching in gate recess and Gate metallization  29

4.5  InAlP schottky diodes  29

4.5.1  The Ti/Pt/Au/InAlP Schottky Metal Structures  30

VII
<table>
<thead>
<tr>
<th>Section</th>
<th>Content</th>
</tr>
</thead>
<tbody>
<tr>
<td>4.5.1-a</td>
<td>Interfacial Properties of Ti/Pt/Au Schottky Contact</td>
</tr>
<tr>
<td>4.5.1-b</td>
<td>Characteristic of Ti/Pt/Au Schottky contact</td>
</tr>
<tr>
<td>4.5.1-c</td>
<td>C-V measurement of Ti/Pt/Au Schottky contact</td>
</tr>
<tr>
<td>4.5.1-d</td>
<td>Sheet resistance of Ti/Pt/Au Schottky contact</td>
</tr>
<tr>
<td>4.5.1-e</td>
<td>TEM image of the annealed Ti/Pt/Au sample after thermal annealing</td>
</tr>
<tr>
<td>4.5.2</td>
<td>The Pt/Ti/Pt/Au/InAlP Schottky Metals Structures</td>
</tr>
<tr>
<td>4.5.2-a</td>
<td>Characteristics of Pt/Ti/Pt/Au Schottky contact</td>
</tr>
<tr>
<td>4.5.2-b</td>
<td>C-V measurement of Pt/Ti/Pt/Au contact</td>
</tr>
<tr>
<td>4.5.2-c</td>
<td>Sheet resistance of Pt/Ti/Pt/Au on InAlP</td>
</tr>
<tr>
<td>4.5.2-d</td>
<td>TEM Image of Pt/Ti/Pt/Au sample after thermal annealing</td>
</tr>
<tr>
<td>4.5.3</td>
<td>The W/Ti/Pt/Au/InAlP Schottky Metal Structures</td>
</tr>
<tr>
<td>4.5.3-a</td>
<td>Interfacial properties of W/Ti/Pt/Au Schottky contact</td>
</tr>
<tr>
<td>4.5.3-b</td>
<td>Characteristics of W/Ti/Pt/Au Schottky contact</td>
</tr>
<tr>
<td>4.5.3-c</td>
<td>C-V measurement of W/Ti/Pt/Au contact</td>
</tr>
<tr>
<td>4.5.3-d</td>
<td>Sheet resistance of W/Ti/Pt/Au on InAlP</td>
</tr>
<tr>
<td>4.6</td>
<td>DC Characteristics of the D-mode and E-mode InAlP PHEMTs with Ti/Pt/Au Gate</td>
</tr>
<tr>
<td>4.7</td>
<td>Effect of gate orientation on InAlP/InGaAs PHEMT characteristics</td>
</tr>
<tr>
<td>4.8</td>
<td>Performance comparison of InAlP/InGaAs PHEMTs</td>
</tr>
</tbody>
</table>
with Ti/Pt/Au, Pt/Ti/Pt/Au and W/Ti/Pt/Au schottky metal contacts under thermal treatments.

4.8.1 Performance of InAlP/InGaAs PHEMTs with Ti/Pt/Au contact

4.8.2 Performance of InAlP/InGaAs PHEMTs with Pt/Ti/Pt/Au contact

4.8.3 Performance of InAlP/InGaAs PHEMTs with W/Ti/Pt/Au contact

Chapter 5 Conclusions

References

Figures

Tables